

Docket No.: 57454-329

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of

Masahiro SHIMIZU, et al.

Serial No.: 10/053,543✓

Group Art Unit: 2814

Filed: January 24, 2002

Examiner: G. Peralta

For: SEMICONDUCTOR DEVICE

AMENDMENT

Commissioner for Patents
Washington, DC 20231

Sir:

The following Amendment and Remarks are submitted in response to the Office Action dated November 20, 2002.

IN THE CLAIMS:

Please amend claim 13 as follows.

13. (Amended) [The method according to claim 12, said source/drain of said second transistor having a highly doped region, wherein:

the step of forming said source/drain of said second transistor includes the step of forming first metal silicide at a surface of said heavily doped region; and

the step of forming said bit line includes the steps of: forming a plug electrode in said first contact hole; forming second metal silicide at a surface of said plug electrode;

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Arnold
SDavis
PATENT 2/25/03

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Rule
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B1 in math A